L Number	Hits	Search Text	DB	Time stamp
1	640	257/77.ccls.	USPAT	2003/10/20 17:59
2	252	257/77.ccls. and diamond	USPAT	2003/10/20 18:00
3	180	(257/678.ccls. or 257/684.ccls. or 257/687.ccls. or	USPAT	2003/10/20 18:02
		257/701.ccls. or 257/702.ccls. or 257/706.ccls. or		
		257/707.ccls. or 257/798.ccls.) and diamond		
4	57	257/713.ccls. and diamond	USPAT	2003/10/20 18:02
.	97	wafer and (diamond with (integrated adj circuit))	USPAT	2002/09/11 18:07
.	36	(wafer and (diamond with (integrated adj circuit))) and	USPAT	2002/09/11 18:13
	00	diamond.ti.	USFAI	2002/09/11 16.13
_	163	(diamond.ti. and diamond) and (heat adj sink)	LICDAT	2002/00/44 40:44
	43	(diamond.ti. and diamond) and (diamond near (heat adj sink))	USPAT	2002/09/11 18:14
	99	(diamond.ti. and diamond) and (diamond hear (fleat adj sink))	USPAT	2002/09/11 18:14
.			USPAT	2003/01/13 16:26
.	82	438/105.ccls. and diamond	USPAT	2002/09/11 20:08
•	14	(diamond and (integrated adj (circuit or circuits))) and (solid	USPAT;	2002/09/29 23:44
		adj diamond)	EPO; JPO;	
1			DERWENT;	
			IBM_TDB	
.	382	438/122.ccis.	USPAT	2002/09/30 02:49
.	27	438/122.ccls. and diamond	USPAT	2002/09/30 01:51
	387	diamond and (monocrystalline adj silicon)	USPAT	2002/09/30 01:52
-	10	(diamond and (monocrystalline adj silicon)) and (heat adj sink)	USPAT	2002/09/30 01:51
	1	(438/122.ccls. and diamond) and (monocrystalline adj silicon)	USPAT	2002/09/30 01:53
_	1	(438/122.ccls. and diamond) and (monocrystalline)	USPAT	2002/09/30 01:54
_	1	(monocrystalline adj silicon) and (diamond adj heat adj sink)	USPAT	2002/09/30 02:43
	3	438/122.ccls. and (monocrystalline adj silicon)	USPAT	2003/10/20 17:58
	113	(monocrystalline adj silicon) and (heat adj sink)	USPAT	,
	23			2002/09/30 03:23
·	23 46	(flip adj chip) and (diamond with (heat adj sink))	USPAT	2002/09/30 03:24
		(monocrystalline adj silicon) with diamond	USPAT	2002/09/30 03:42
	101	438/105.ccls.	USPAT	2003/01/13 16:27
	83	438/105.ccls. and diamond	USPAT	2003/01/13 16:48
- 1	596	257/77.ccls.	USPAT	2003/10/20 17:59
	242	257/77.ccls. and diamond	USPAT	2003/01/13 16:53
-	151	(257/678.ccls. or 257/684.ccls. or 257/687.ccls. or	USPAT	2003/10/20 18:00
		257/701.ccls. or 257/702.ccls. or 257/706.ccls. or		
		257/707.ccls. or 257/798.ccls.) and diamond		
-	32	((257/678.ccls. or 257/684.ccls. or 257/687.ccls. or	USPAT	2003/01/13 17:11
		257/701.ccis. or 257/702.ccls. or 257/706.ccls. or		
		257/707.ccls. or 257/798.ccls.) and diamond) and (CVD or		
		(chemical adj vapor adj deposition))]
_ }	15	(((257/678.ccls. or 257/684.ccls. or 257/687.ccls. or	USPAT	2003/01/14 13:54
		257/701.ccls. or 257/702.ccls. or 257/706.ccls. or	00.7	
ļ		257/707.ccls. or 257/798.ccls.) and diamond) and (CVD or		
		(chemical adj vapor adj deposition))) and (silicon with		
	444	diamond)	LICDAT	0000/04/44 45:50
-	414	((((semiconductor and diamond) and silicon) and	USPAT	2003/01/14 15:58
		(monocrystalline or monocrystal or (single adj crystal))) not		
		(diamond adj saw)) and ((CVD or (chemical adj vapor adj		
i		deposit\$3)) with diamond)		
.	179	117/929.ccls.	USPAT	2003/01/14 16:51
.	708	257/713.ccls.	USPAT	2003/01/14 19:31
	56	257/713.ccls. and diamond	USPAT	2003/10/20 18:02
-	493	257/713.ccls. not (257/678.ccls. or 257/684.ccls. or	USPAT	2003/01/14 19:31
		257/687.ccls. or 257/701.ccls. or 257/702.ccls. or		
		257/706.ccls. or 257/707.ccls. or 257/798.ccls.)		
	31	(257/713.ccls. not (257/678.ccls. or 257/684.ccls. or	USPAT	2003/01/14 19:31
	01	257/687.ccls. or 257/701.ccls. or 257/702.ccls. or	30. /	
		257/706.ccls. or 257/707.ccls. or 257/798.ccls.)) and diamond	ŀ	1